

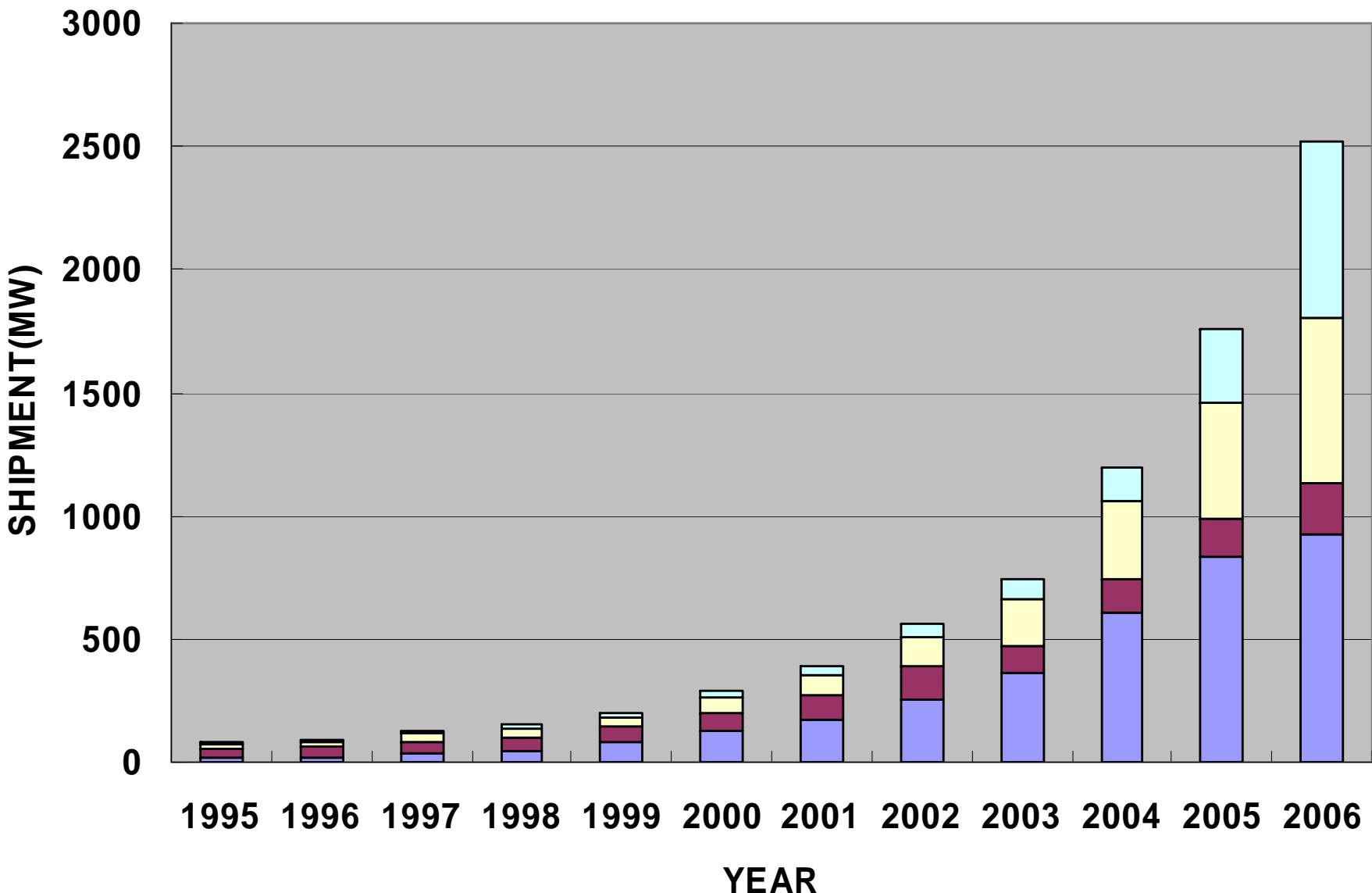
太陽光発電技術開発の現状と将来展望 —2050年に向けて

**"Present Status and Future Prospects of Photovoltaics
- Toward 2050"**

*Prof. Makoto KONAGAI
Department of Physical Electronics,
Tokyo Institute of Technology*

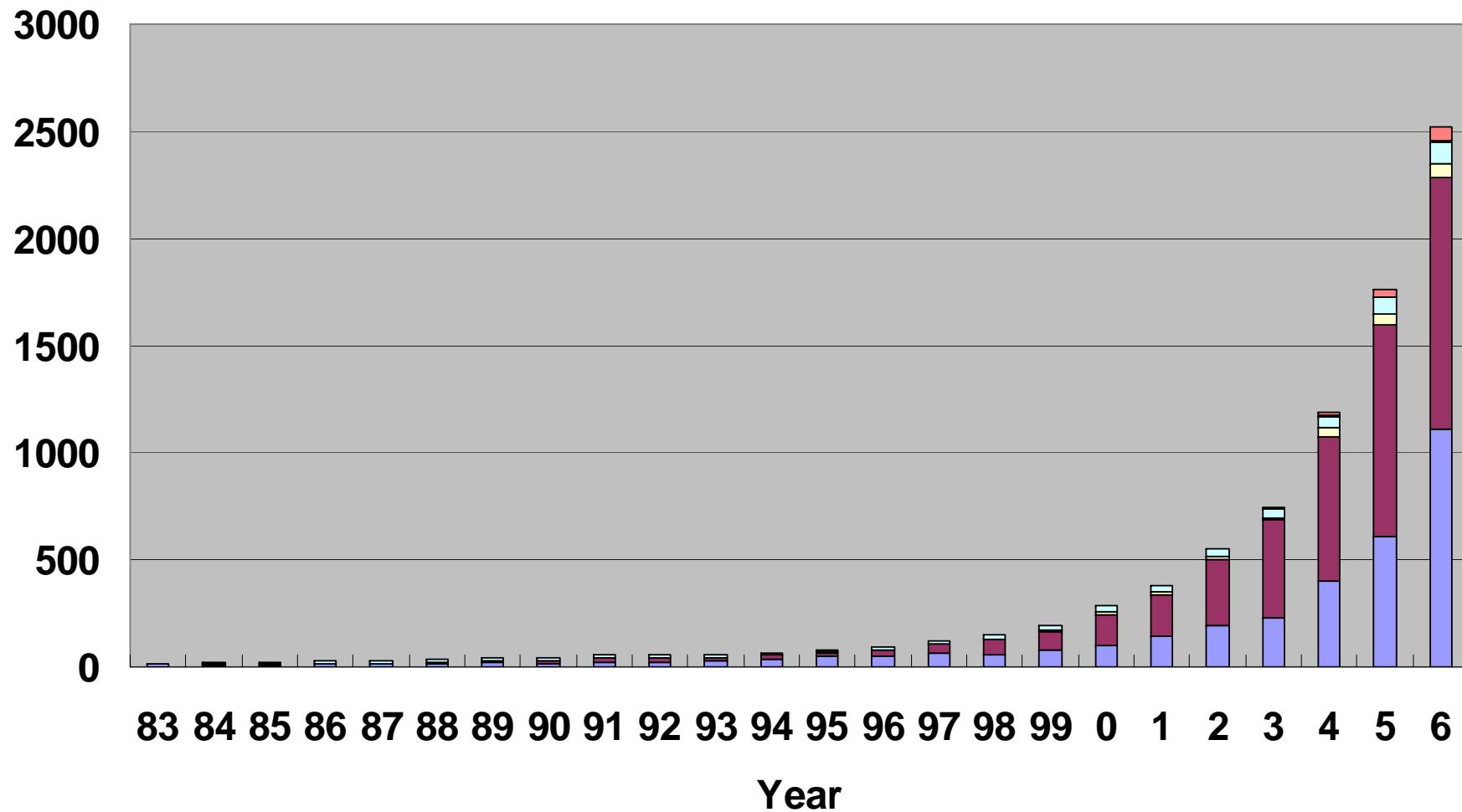
World Shipment of Solar Cells

■ Japan ■ U.S.A. ■ EU ■ Others

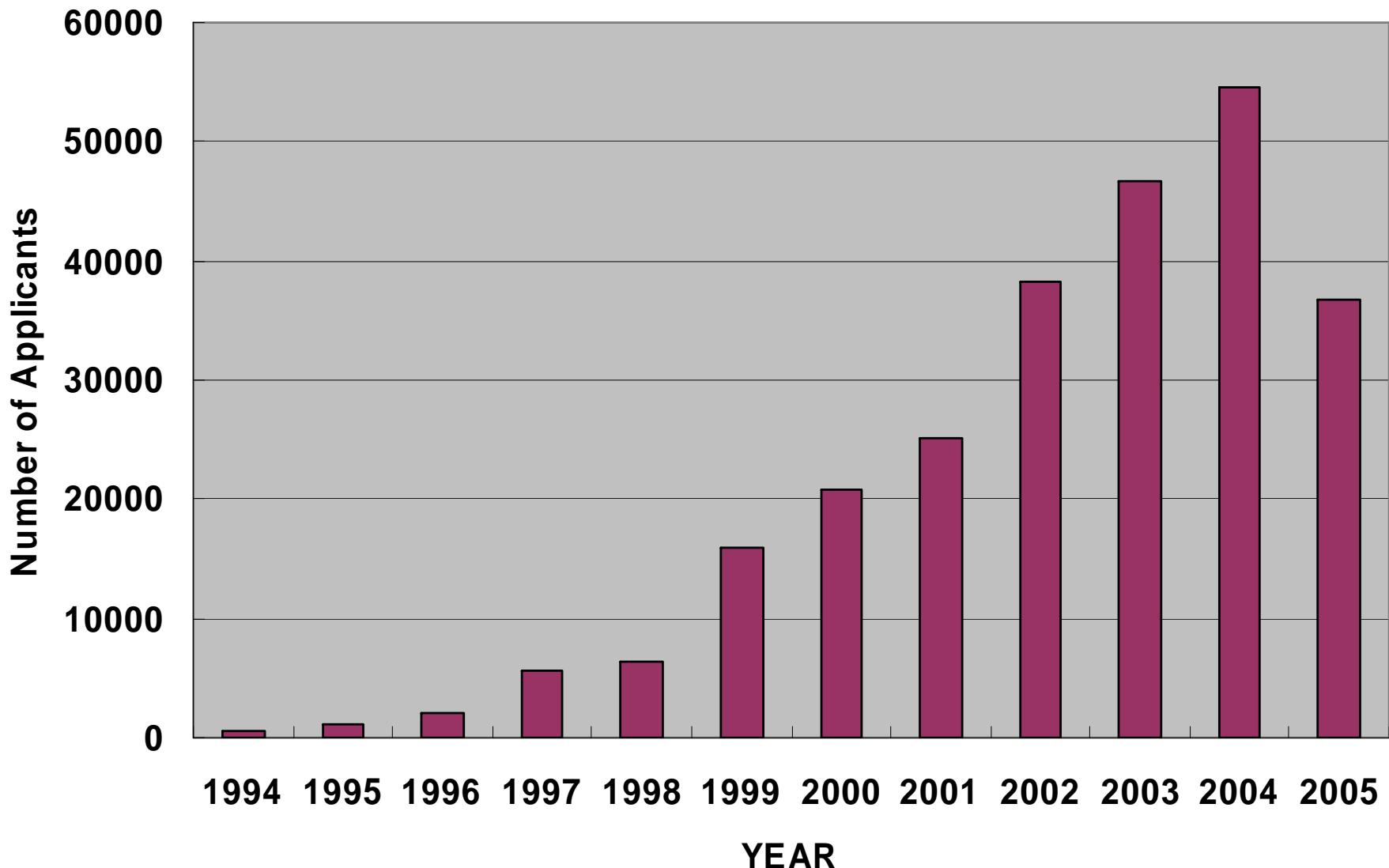


World Shipment of Solar Cells

■ single c-Si ■ cast Si ■ Si ribbon ■ Si thin film ■ CIS ■ CdTe

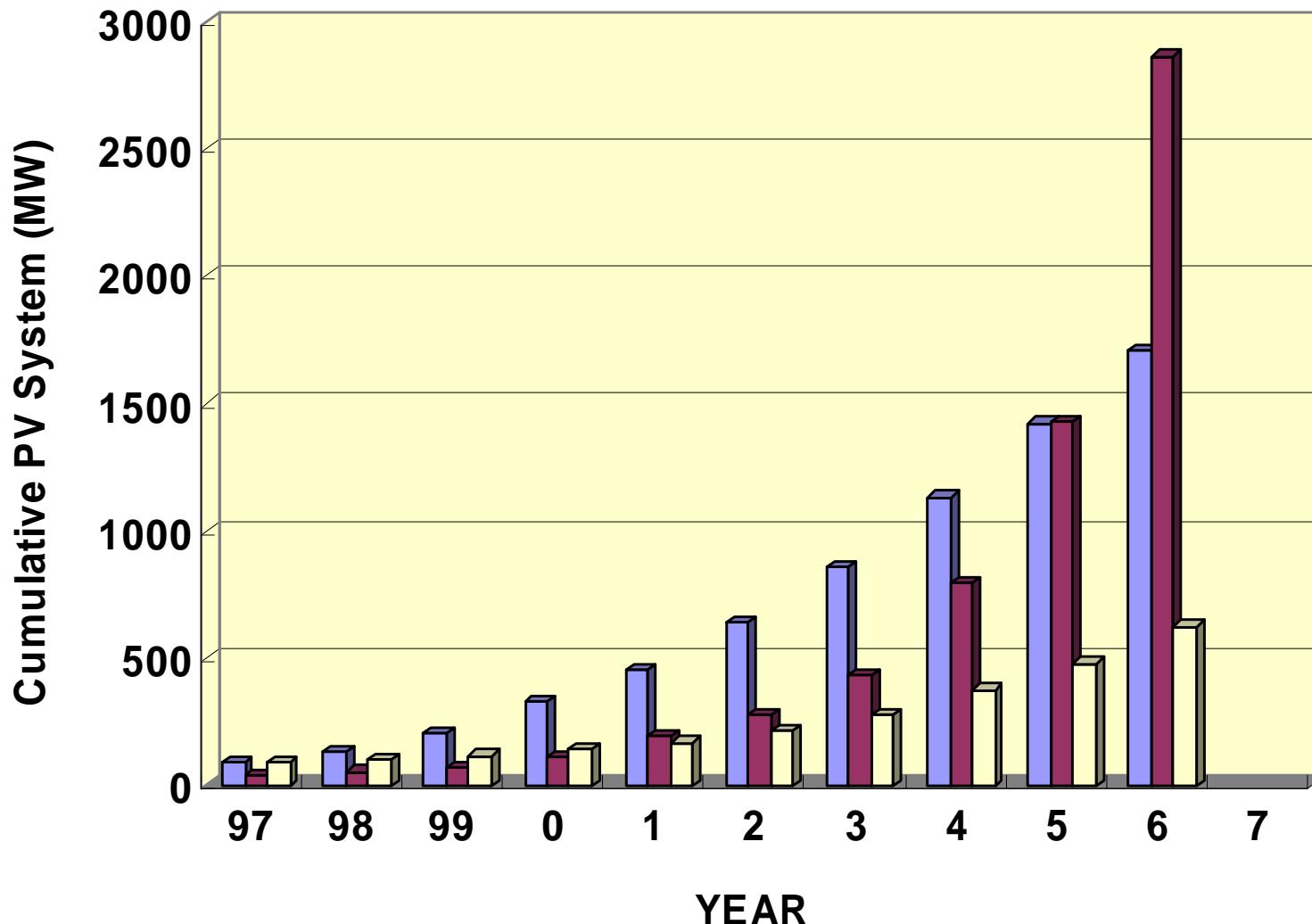


Number of Applicants for Residential PV Subsidy Program

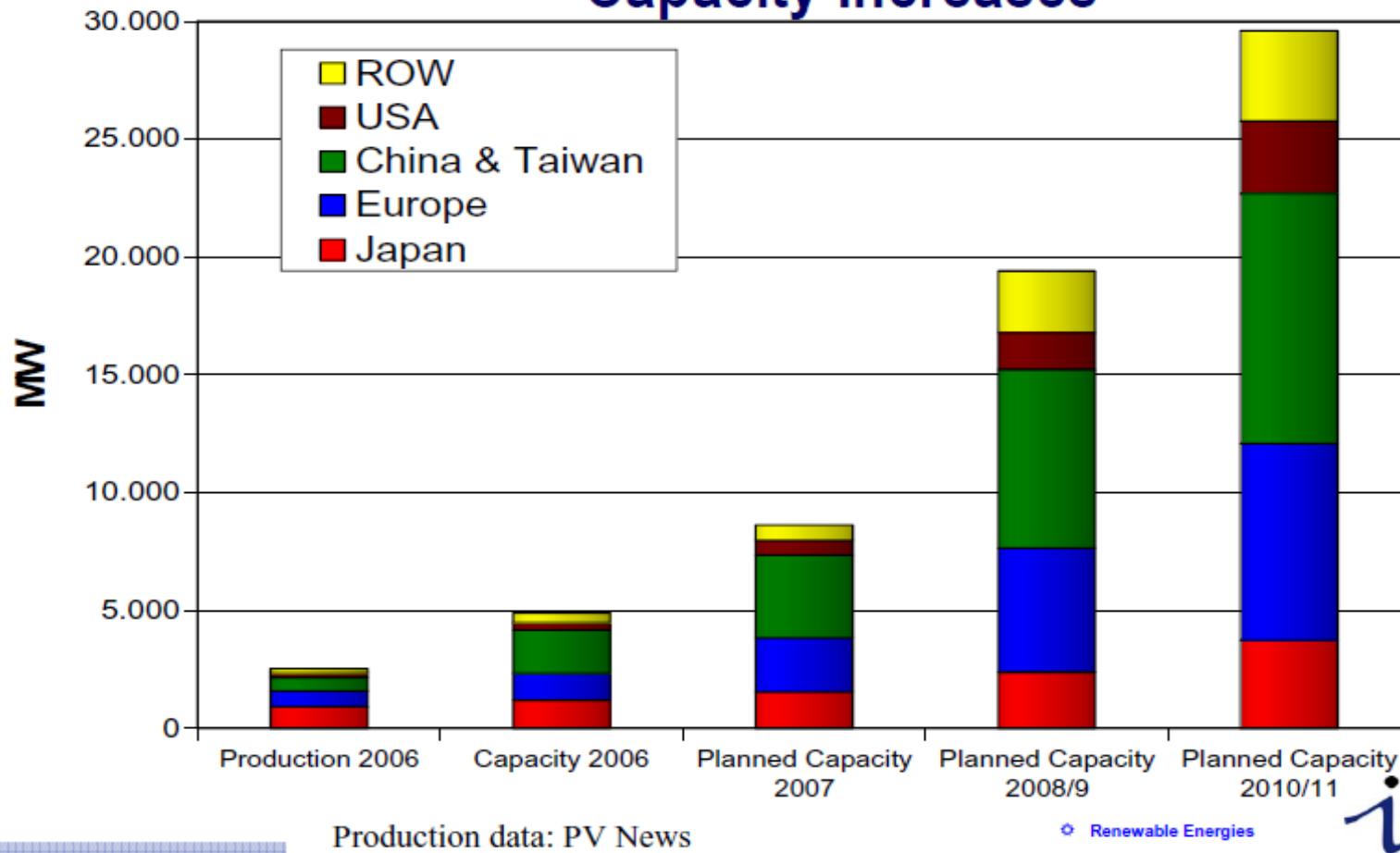


Cumulative PV System

■ Japan ■ Germany ■ USA

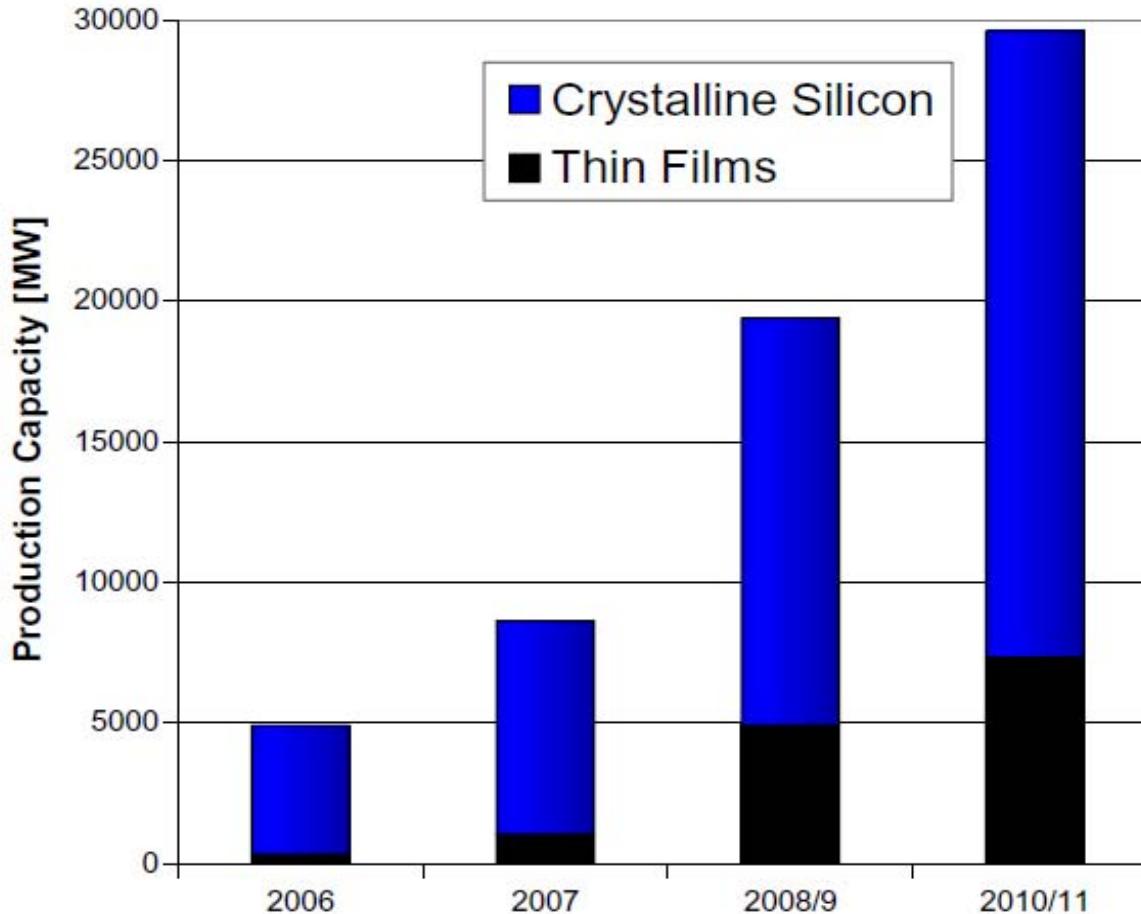


World-wide PV Production 2006 and Announced Capacity Increases



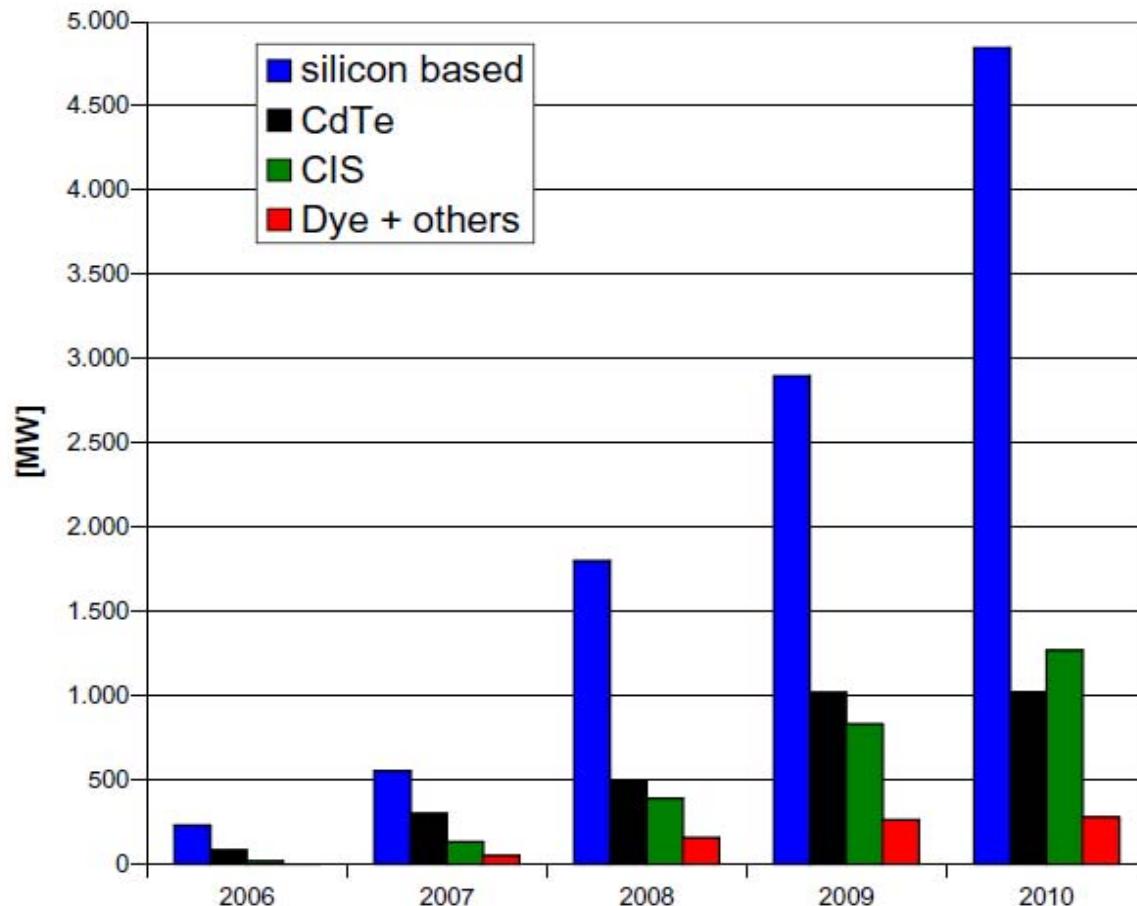
Production data: PV News

© Renewable Energies



Announced
Capacity
Increases

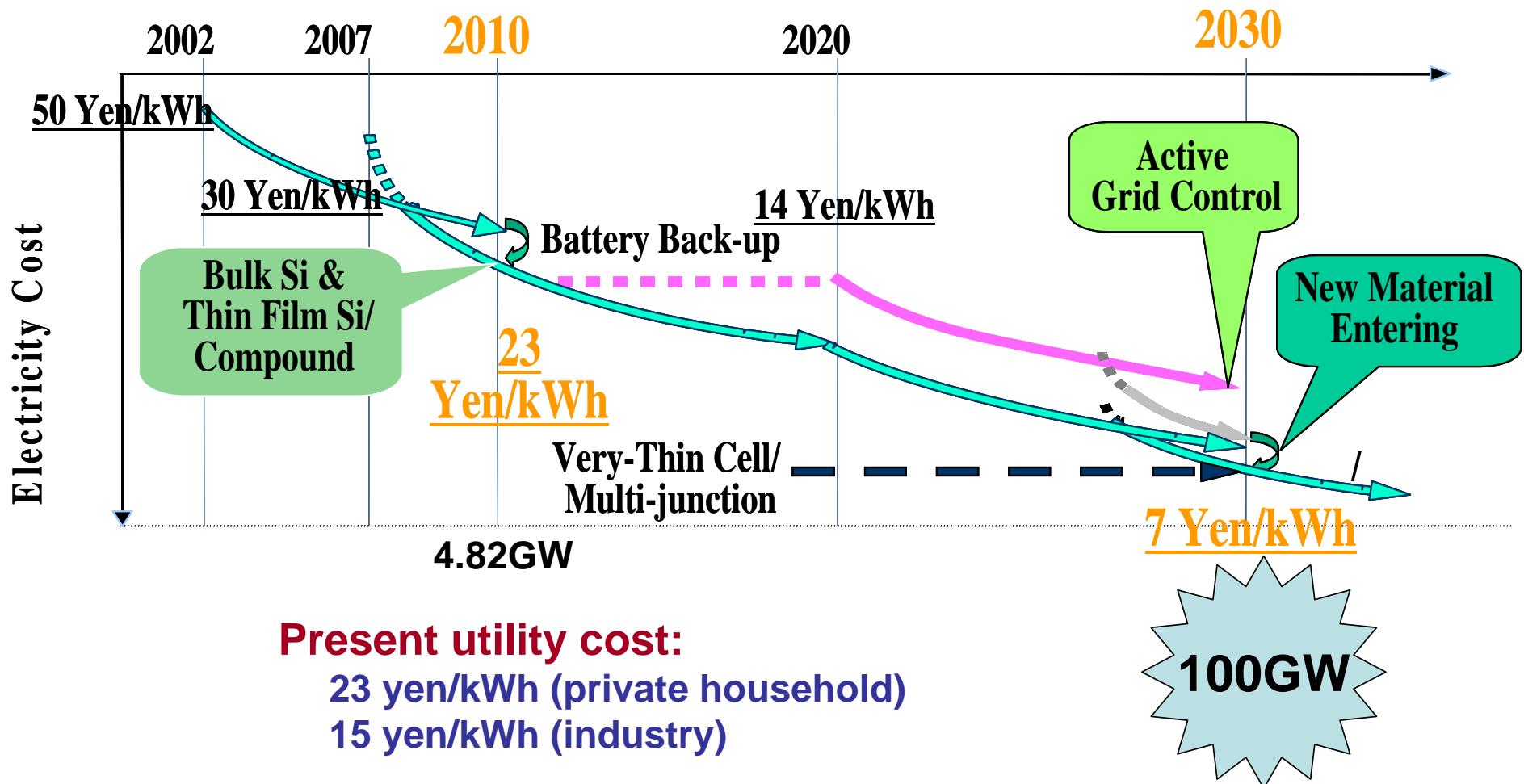
Renewable Energies



Announced Production Capacities by Technology

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Japanese PV Roadmap until 2030



Electricity generation cost:
5-6 yen/kWh (Nuclear)
9 yen/kWh (hydro)

1US\$= 120 JPY

Japanese PV Roadmap until 2030 (NEDO)

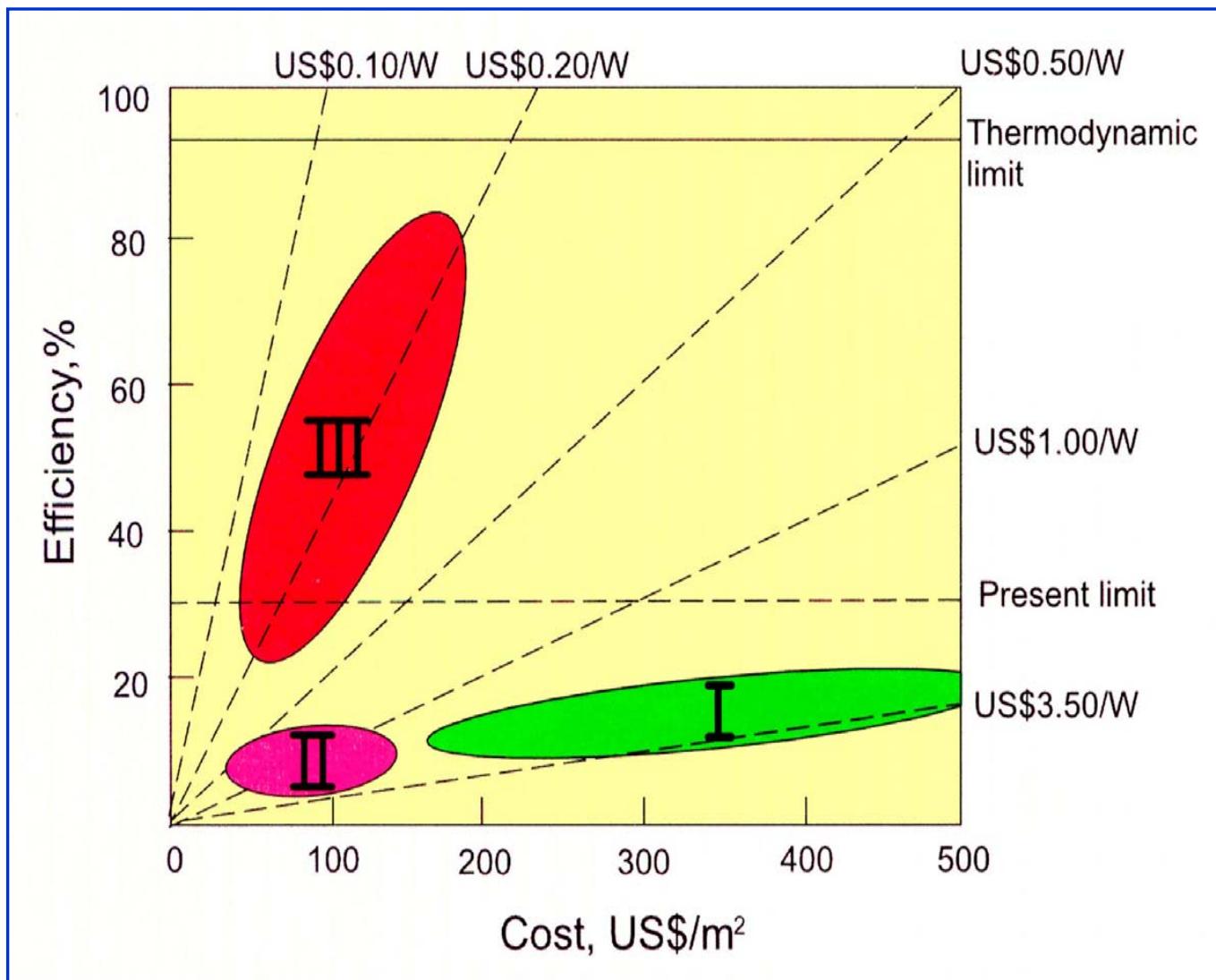
| Item | Target (Target Year) |
|------------------------|---|
| Module Cost Reduction | 100 yen/W (2010), 75 yen/W(2020) <50 yen/W(2030) |
| Module Durability | 30 Year Life (2020) |
| Stable Material Supply | Unit Si Consumption:1g/W (2030) |
| Inverter Cost | 15,000 yen/kW (2020) |
| Storage Battery | 10 yen/Wh (2020) |

Module efficiency target(%) (production level) (Cell efficiency)

| Cell Type | 2010 | 2020 | 2030 |
|----------------------|--------|--------|--------|
| Thin-Bulk Multi-c-Si | 16(20) | 19(25) | 22(25) |
| Thin-Film Si | 12(15) | 14(18) | 18(20) |
| CIS Type | 13(19) | 18(25) | 22(25) |
| Super-High η | 28(40) | 35(45) | 40(50) |
| Dye-sensitized | 6(10) | 10(15) | 15(18) |

Cost/Efficiency of Photovoltaic Technology

Prof.M.Green, “the third generation PV”

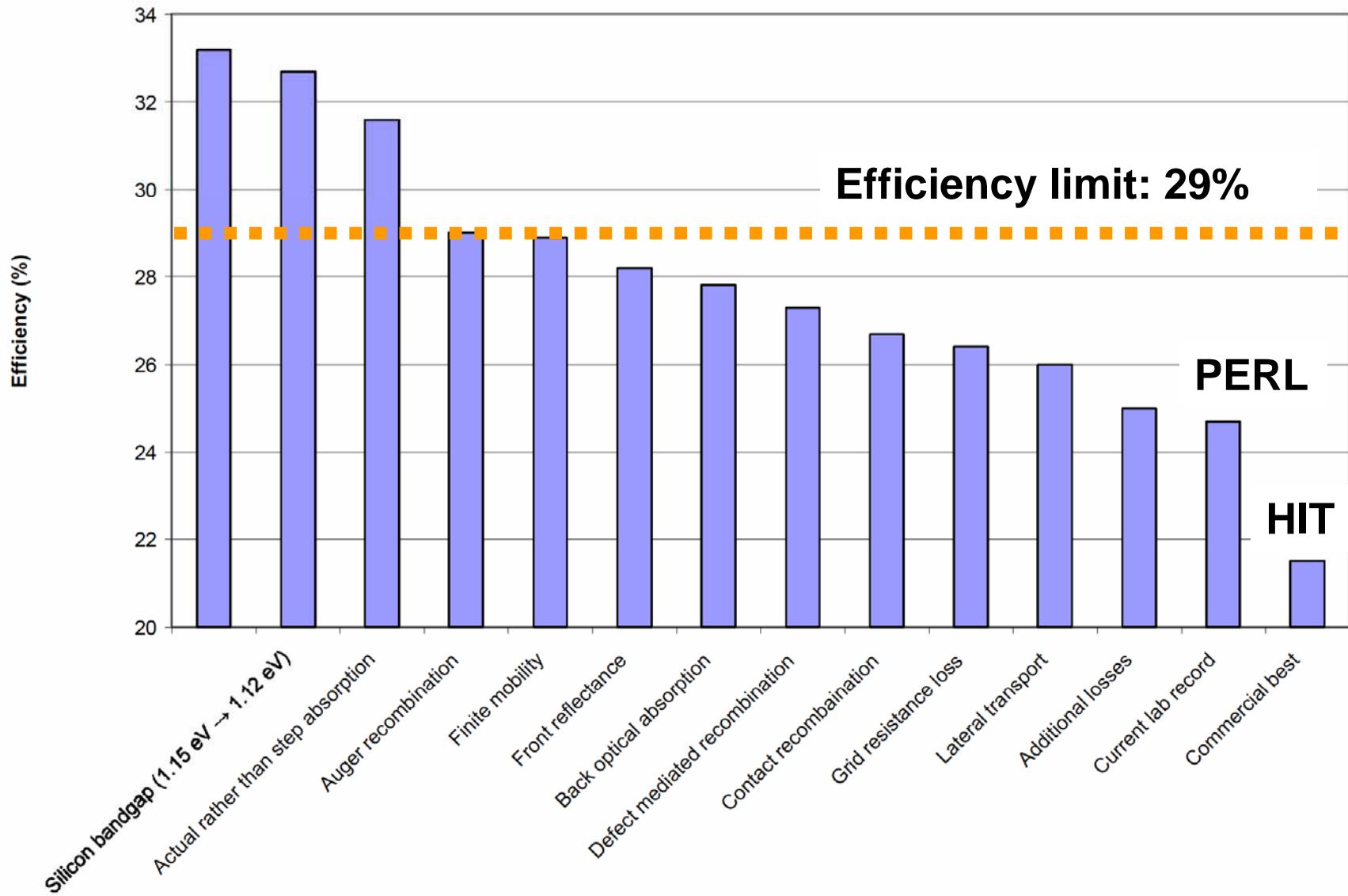


Confirmed terrestrial cell and submodule efficiencies measured under the global AM1.5 spectrum(1000W/m²) at 25°C (Progress in Photovoltaics)

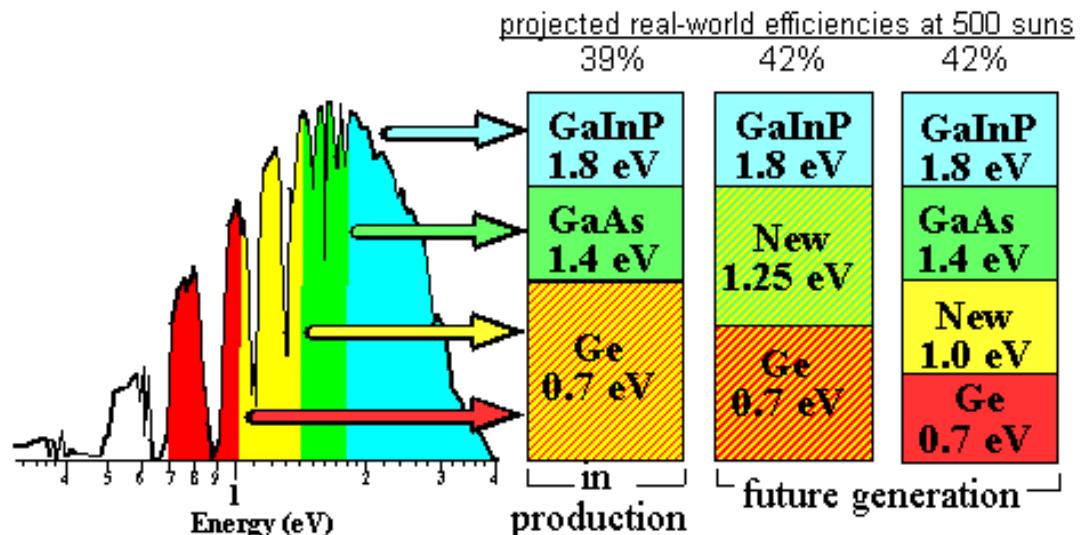
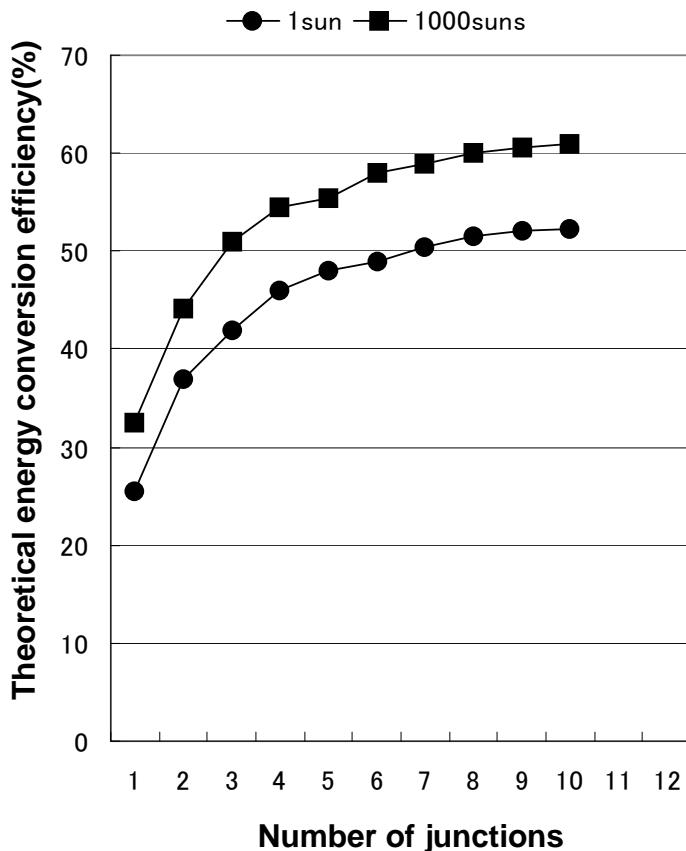
| Classification | Effic. (%) | Area (cm ²) | Voc (V) | Jsc (mA/cm ²) | FF (%) | Test Center (and date) | Description |
|-----------------------------|---------------|----------------------------|------------|------------------------------|-----------|---------------------------|----------------------------|
| Si(crystalline) | 24.7±0.5 | 4.00(da) | 0.706 | 42.2 | 82.8 | Sandia(3/99) | UNSW PERL |
| Si(multicrystalline) | 20.3±0.5 | 1.002(ap) | 0.664 | 37.7 | 80.9 | NREL(5/04) | FhG-ISE |
| Si(thin-film transfer) | 16.6±0.4 | 4.017(ap) | 0.645 | 32.8 | 78.2 | FhG-ISE(7/01) | U.Stuttgart (45µm thick) |
| Si(thin-film submodule) | 9.4±0.3 | 94.9(ap) | 0.493 | 26/0 | 73.1 | Sandia(4/06) | CSG Solar (1-2µm on glass) |
| GaAs(crystalline) | 25.1±0.8 | 3.91(t) | 1.022 | 28.2 | 87.1 | NREL(3/90) | Kopin, AlGaAs window |
| GaAs(thin film) | 24.5±0.5 | 1.002(t) | 1.029 | 28.8 | 82.5 | FhG-ISE(5/05) | Radboud U.,NL |
| GaAs(multicrystalline) | 18.2±0.5 | 4.011(t) | 0.994 | 23.0 | 79.7 | NREL(11/95) | RTI,Ge substrate |
| InP(crystalline) | 21.9±0.7 | 4.02(t) | 0.878 | 29.3 | 85.4 | NREL(4/90) | Spire,epitaxial |
| CIGS(cell) | 18.4±0.5 | 1.04(t) | 0.669 | 35.7 | 77.0 | NREL(2/01) | NREL,CIGS on glass |
| CIGS(submodule) | 16.6±0.4 | 16.0(ap) | 2.643 | 8.35 | 75.1 | FhG-ISE(3/00) | U.Uppsala, 4 serial cells |
| CdTe(cell) | 16.5±0.5 | 1.132(ap) | 0.845 | 26.7 | 75.5 | NREL(9/01) | NREL, mesa on glass |
| Si(amorphous) | 9.5±0.3 | 1.070(ap) | 0.859 | 17.5 | 63.0 | NREL(4/03) | U.Neuchatel |
| Si(nanocrystalline) | 10.1±0.2 | 1.199(ap) | 0.539 | 24.4 | 76.6 | JQA(12/97) | Kaneka (2µm on glass) |
| Dye sensitized | 10.4±0.3 | 1.004(ap) | 0.729 | 21.8 | 65.2 | AIST(8/05) | Sharp |
| Dyesensitized(submodule) | 6.3±0.2 | 26.5(ap) | 6.145 | 1.70 | 60.4 | AIST(8/05) | Sharp |
| Organic polymer | 3.0±0.1 | 1.001(ap) | 0.538 | 9.68 | 52.4 | ASIT(3/06) | Sharp,fullerene derivative |
| GalnP/GaAs | 30.3 | 4.0(t) | 2.488 | 14.22 | 85.6 | JQA(4/96) | Japan Energy |
| GalnP/GaAs/Ge | 32.0±1.5 | 3.989(t) | 2.622 | 14.37 | 85.0 | NREL(1/03) | Spectrolab(monolithic) |
| GaAs/CIS(thin film) | 25.8±1.3 | 4.00(t) | | | | NREL(11/89) | Kopin/Boeing |
| a-Si/CIGS(thin film) | 14.6±0.7 | 2.40(ap) | | | | NREL(6/88) | ARCO |
| a-Si/µc-Si (thin submodule) | 11.7±0.4 | 14.23(ap) | 5.462 | 2.99 | 71.3 | AIST(9/04) | Kaneka(thin film) |

Approaching the 29% limit efficiency of Silicon solar cells

R.M.Swanson, SunPower Corporation



How to improve energy conversion efficiencies - I. multijunction



GaInP/GaAs/Ge triple-junction solar cells:

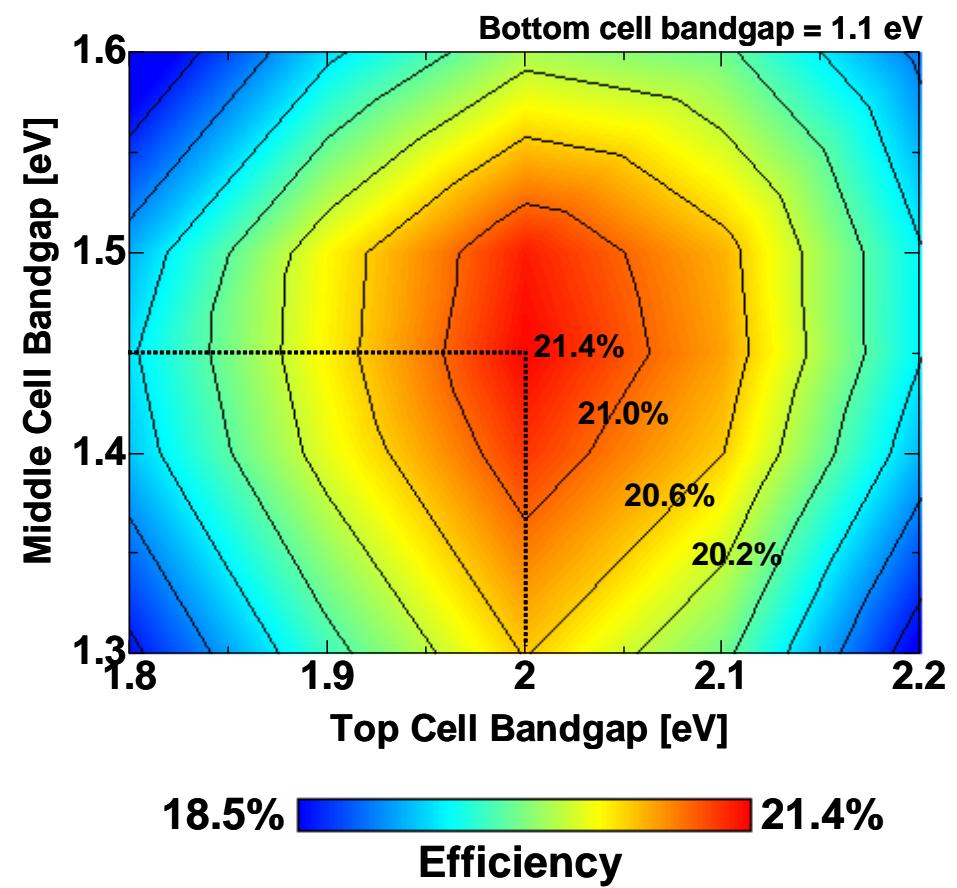
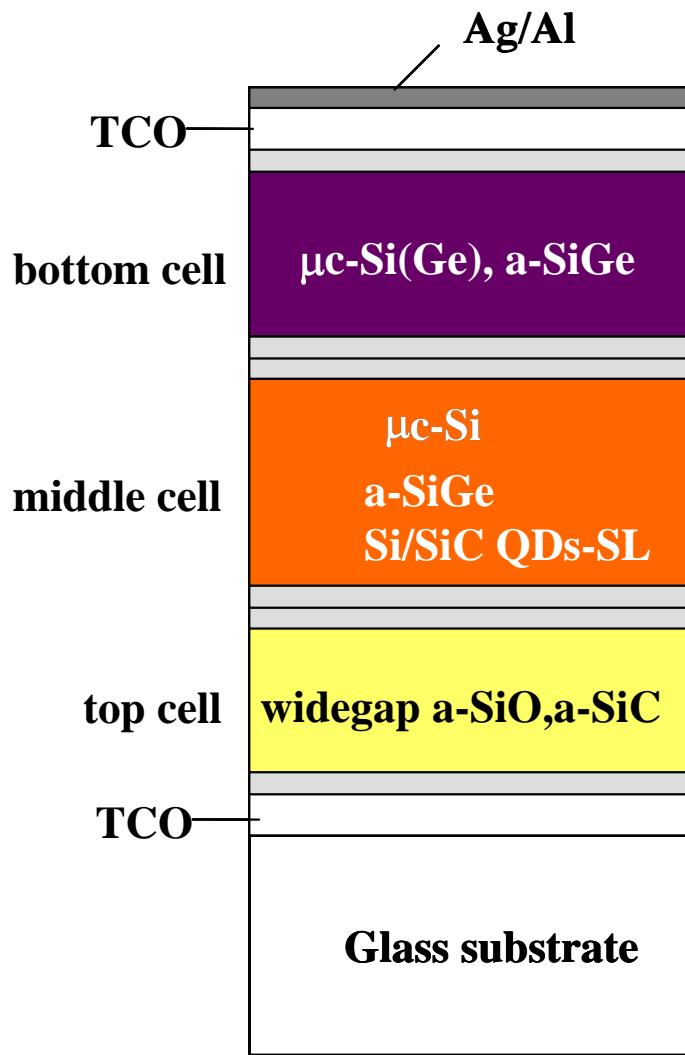
An efficiency of 40.7% for 240 suns
has been demonstrated by Spectrolab.

A.Bennett and L.C.Olsen,

13th IEEE PVSC, Washington,D.C.,(1978)

868

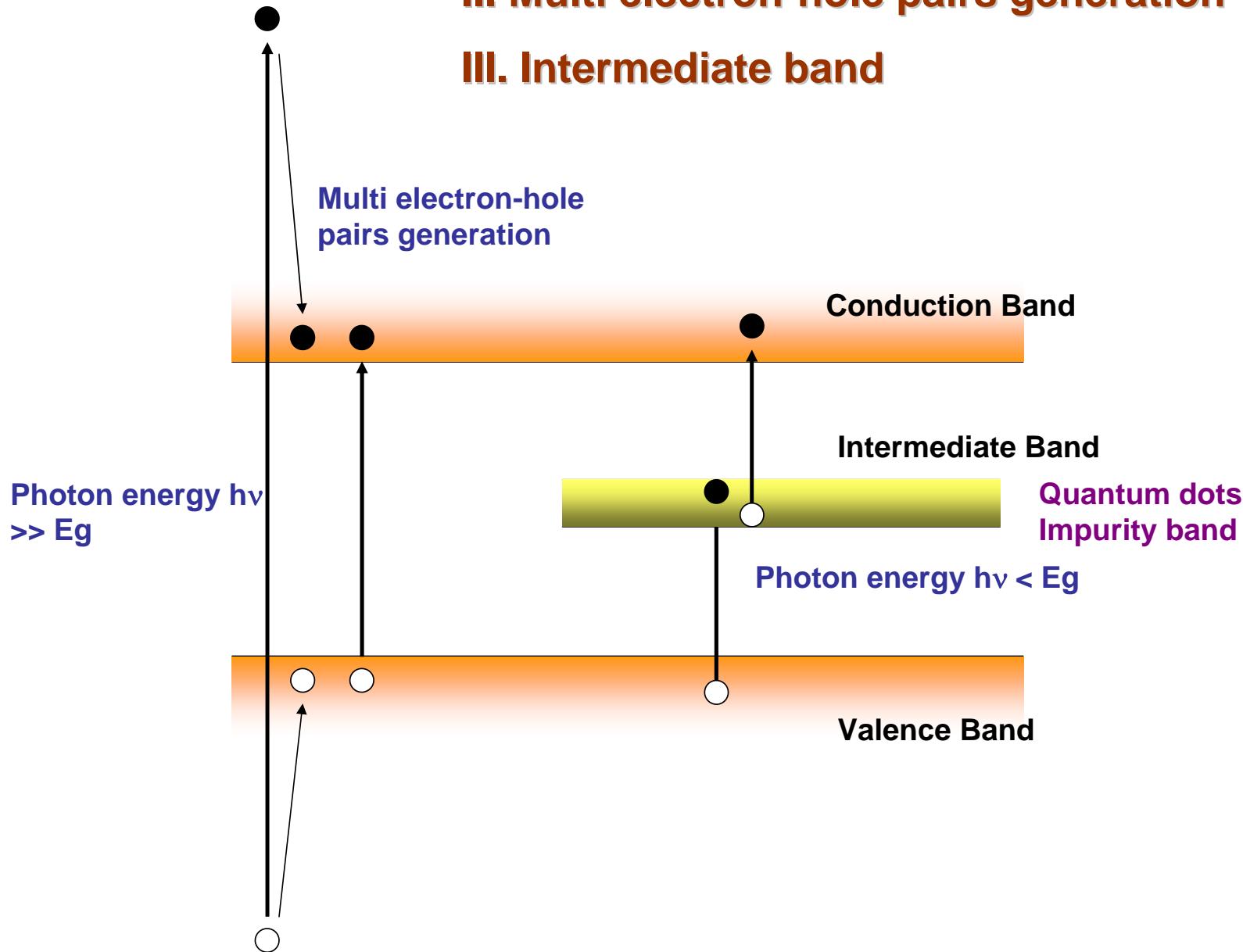
Theoretical Analysis of Triple-Junction Thin-Film Solar Cells



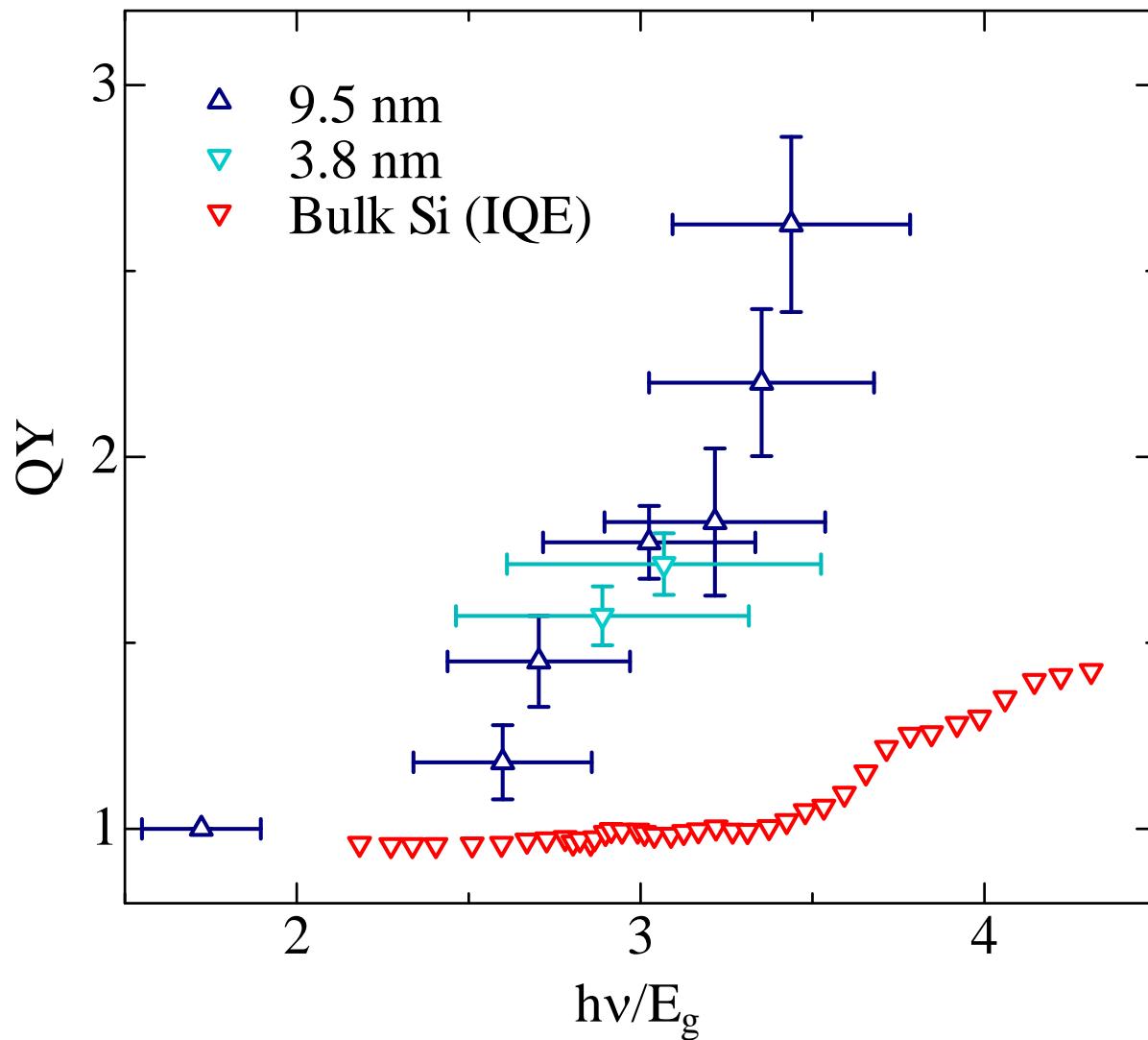
How to improve energy conversion efficiencies

II. Multi electron-hole pairs generation

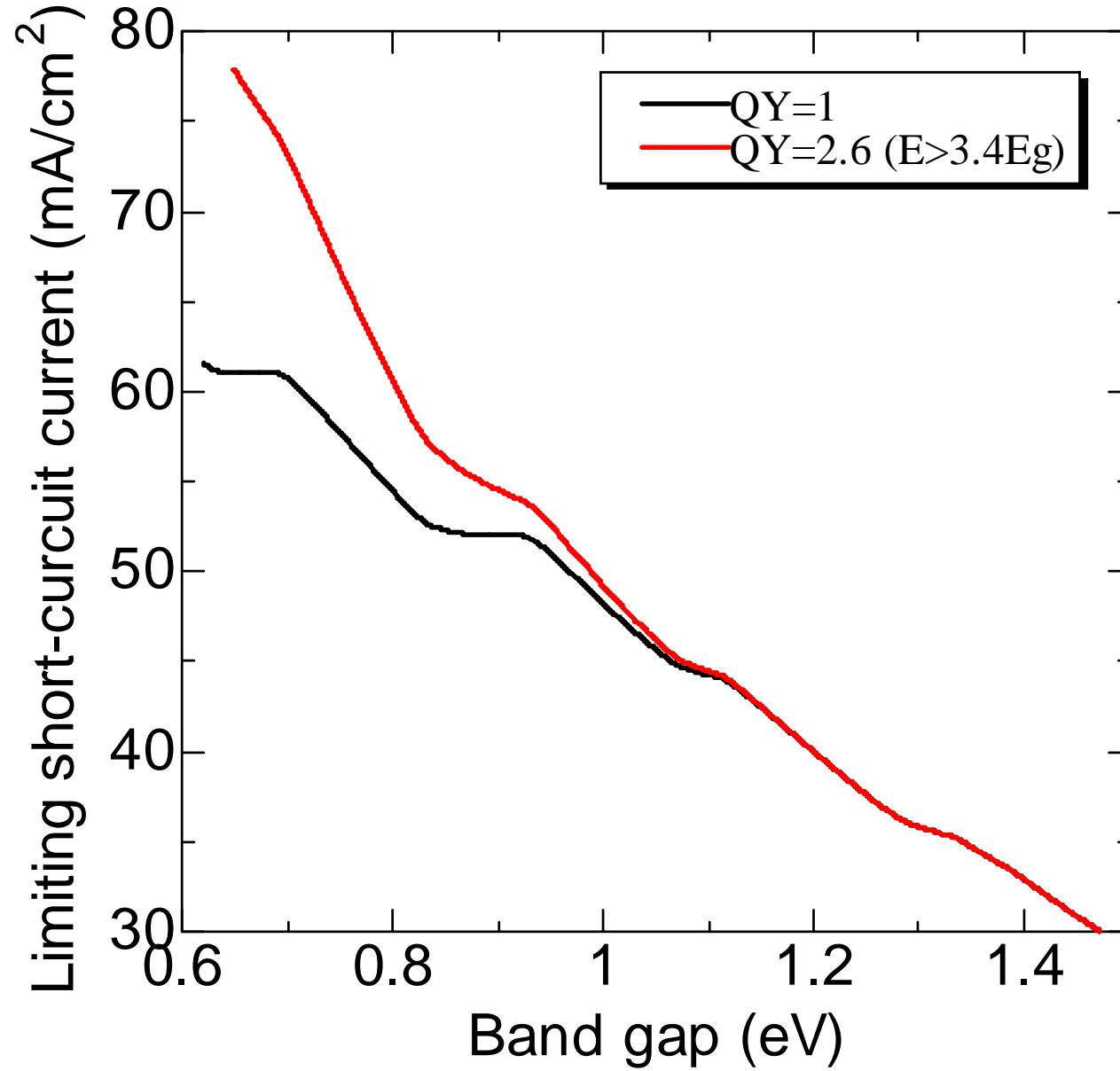
III. Intermediate band



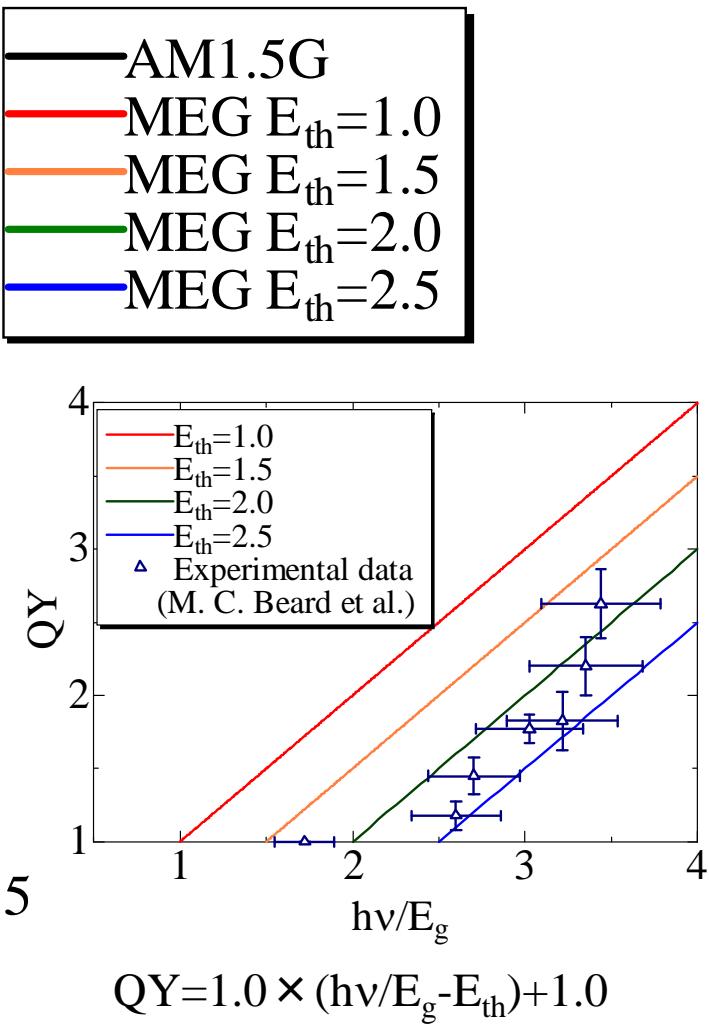
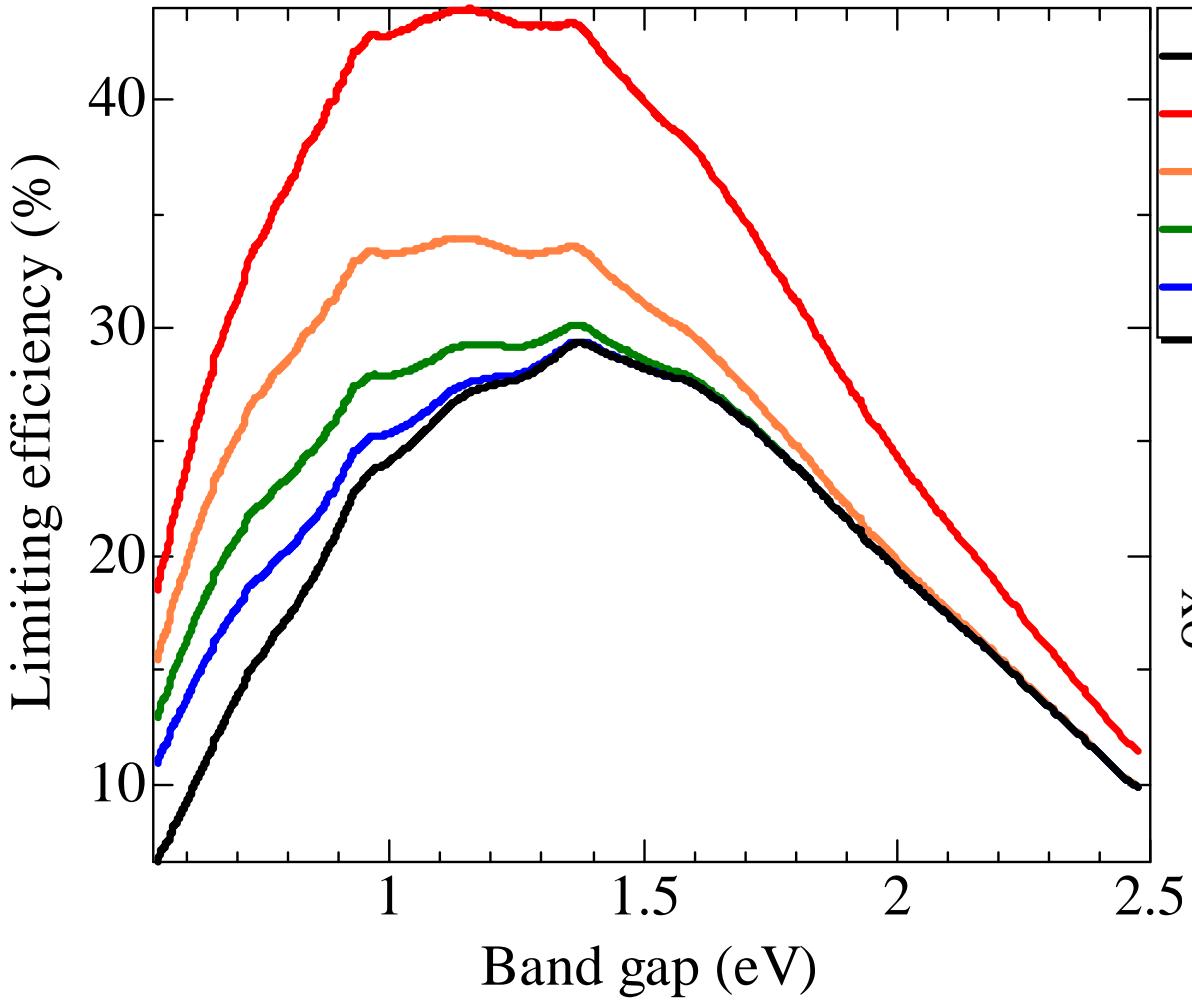
Demonstration of multi-exciton generation



M. C. Beard, K. P. Knutsen, P. Yu, J. M. Luther, Q. Song, W. K. Metzger, R. J. Ellingson, and A. J. Nozik: Nano Letters 7 (2007) 2506.

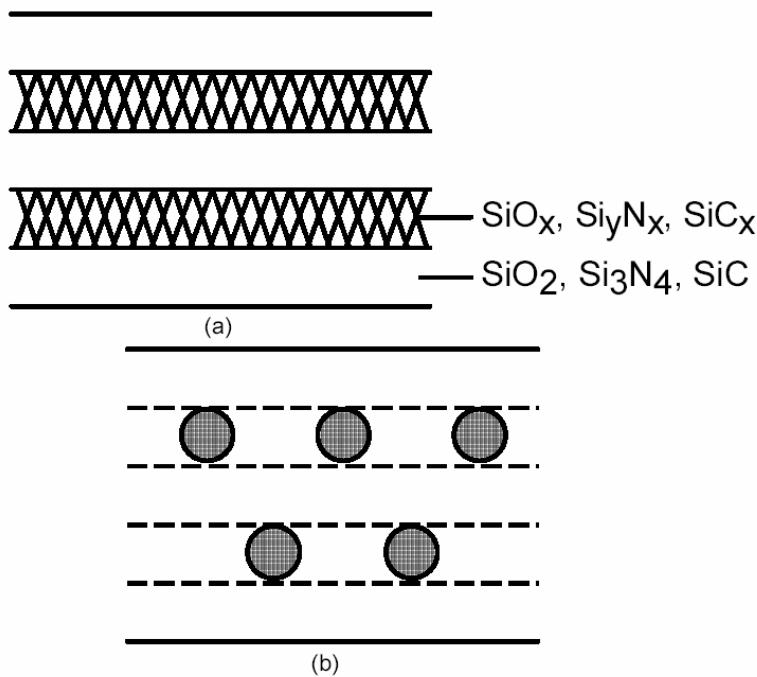


Theoretical limit of energy conversion efficiencies of single-junction solar cells based on multi-exciton generation

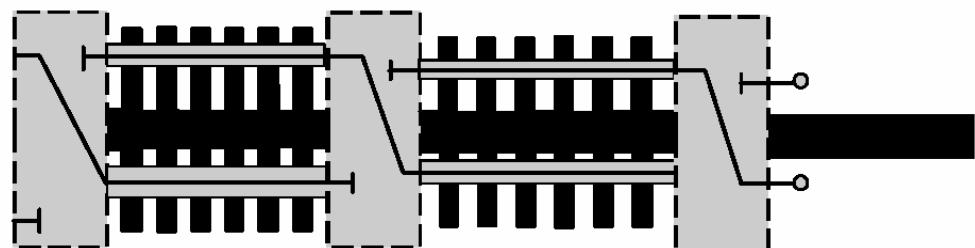


$$QY = 1.0 \times (h\nu/E_g - E_{th}) + 1.0$$

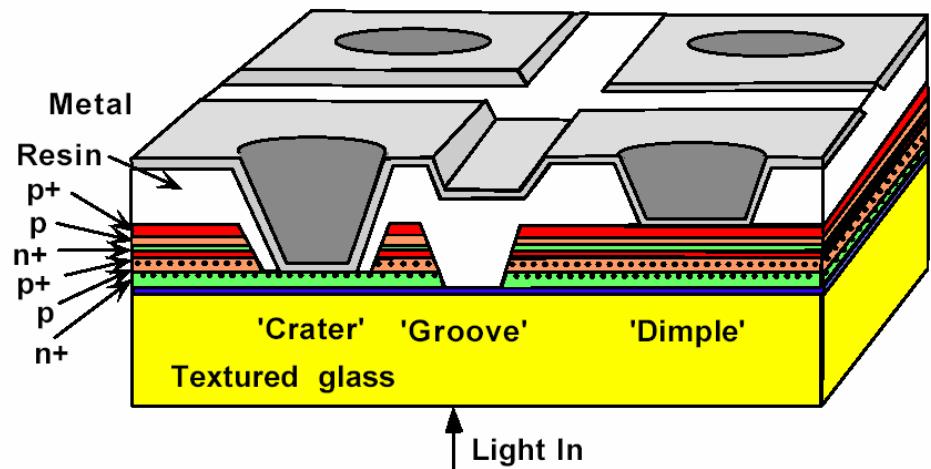
THIRD GENERATION PHOTOVOLTAICS (Prof.M.Green)



(a) Deposition of stoichiometric regions separated by silicon-rich regions; (b) segregation into spherical silicon quantum dots on heating.

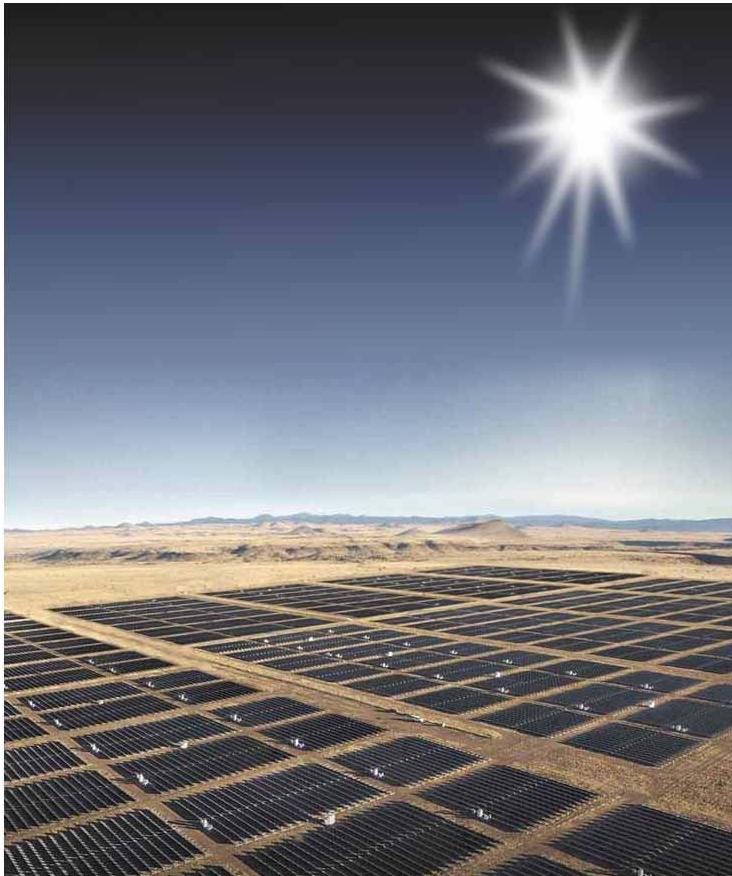


All-Silicon Quantum Dot Superlattice Tandem Cell (SQOT).



CSG 2-cell SWOT interconnection scheme.

Additional proposal: Nano-Based Solar Energy Materials and Solar Cells for Low Latitudes Application



**Photovoltaic system in low latitudes
(by courtesy of Prof.Kurokawa)**

In Japan, photovoltaic systems with a capacity of 100 GW will be installed by 2030. This number is equal to a 1 kW solar power generation per one citizen.

Let us consider that solar cells with a cumulative capacity of 1 kW will be needed for one person in the world on average. According to an estimation of United Nations (UN), the world population will be about 9.3 billion in 2050. Simply saying that the world population in 2050 will be 10 billion, then solar cells with a capacity of 10 billion kW (10 TW) will be required.

Where should we install these 10 TW photovoltaic systems? In general, the PV systems should be installed close to the users. Based on the prediction of the UN, from these 10 billion world population, 5.4 billion of them are the Asian population. Hence, most of the PV systems will be installed in the Asia region, particularly in the low latitudes region.

The development of solar energy materials for applications in the low latitudes region, the research on physics and optimum design of solar cells, the demonstration and fabrication of solar cells, as well as the research on PV system applications, will be required.